

N-Channel Enhancement Mode MOSFET

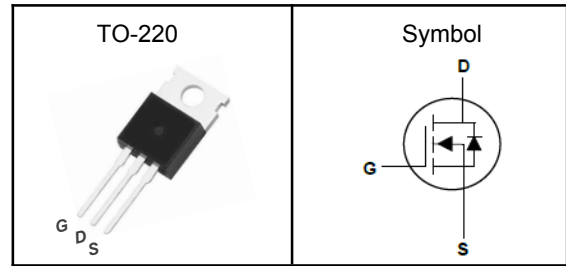
Features

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant
- 100% UIS and Rg Tested

Applications

- Power Management in Desktop Computer
- DC/DC Converters

Pin Description



V_{DSS}	900	V
$R_{DS(ON)-Typ}$	0.95	Ω
I_D	9	A

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V_{DSS}	Drain-Source Voltage	900	V
V_{GSS}	Gate-Source Voltage	± 30	V
T_J	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Single Pulse Avalanche Energy ^③	500	mJ
$I_{DM}^{①}$	Pulse Drain Current Tested	36	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ^①	62.5	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ^①	2.4	$^\circ\text{C}/\text{W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C .

Note ③ : Surface Mounted on 1in^2 FR-4 board with 1oz.



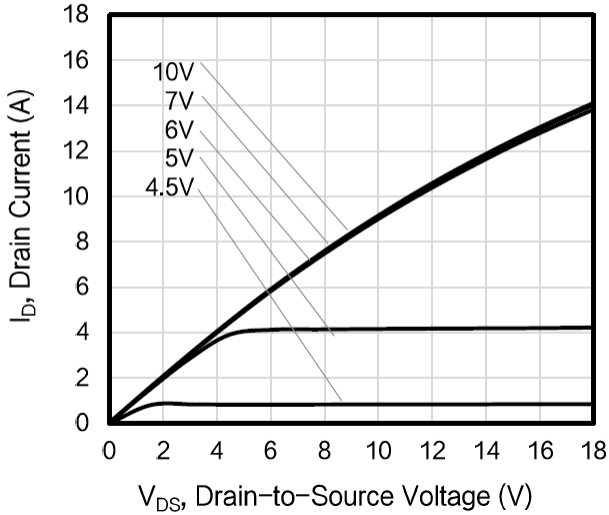
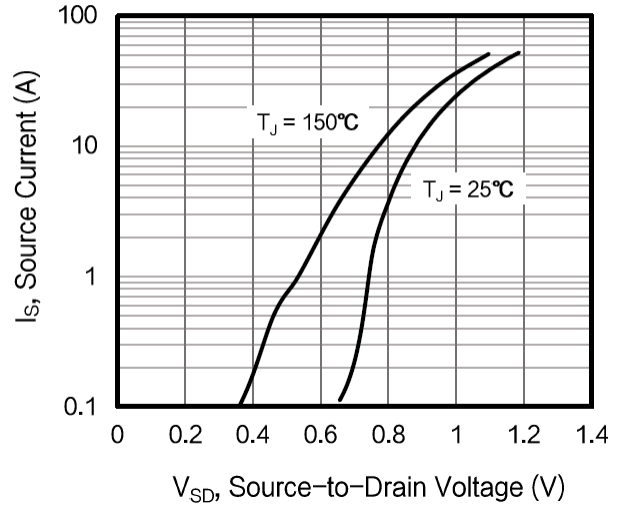
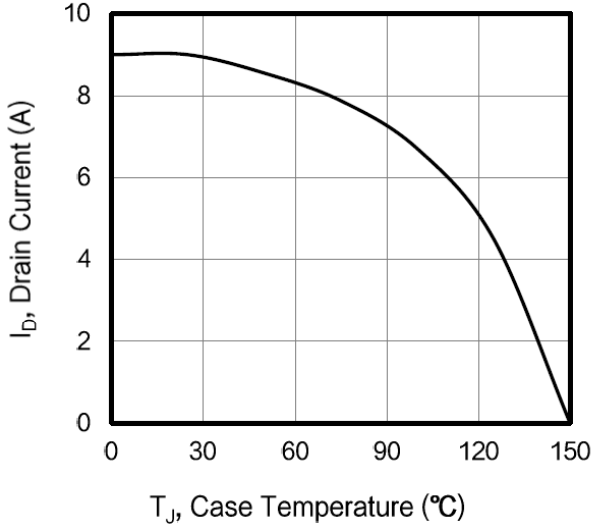
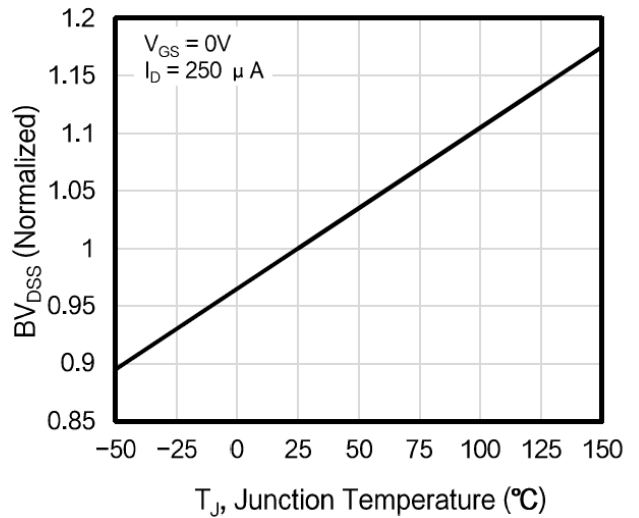
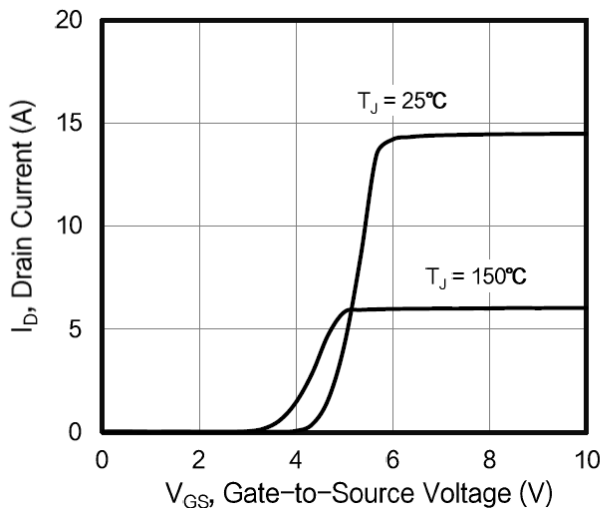
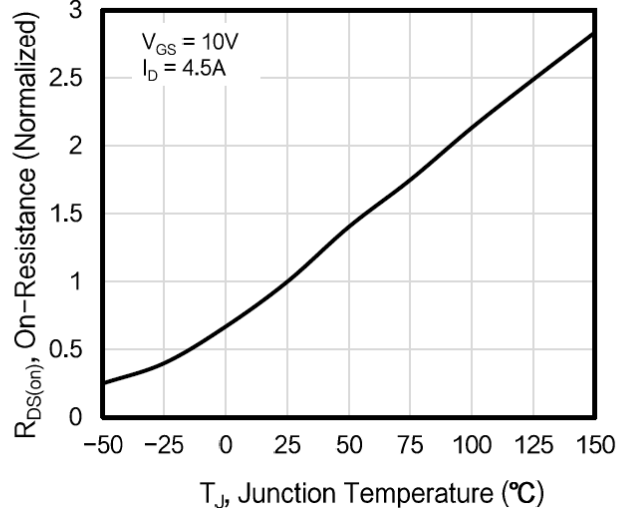
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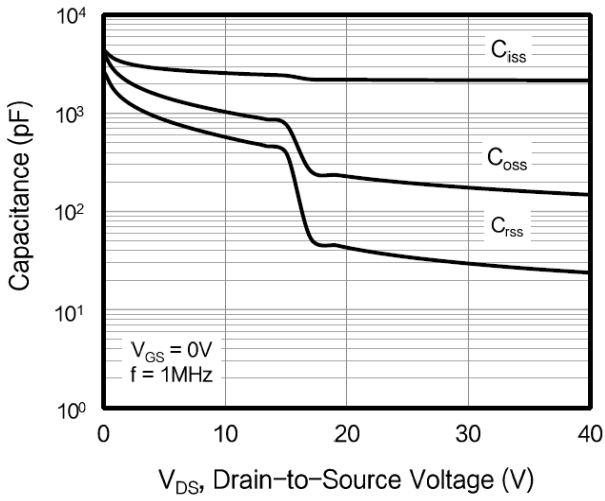
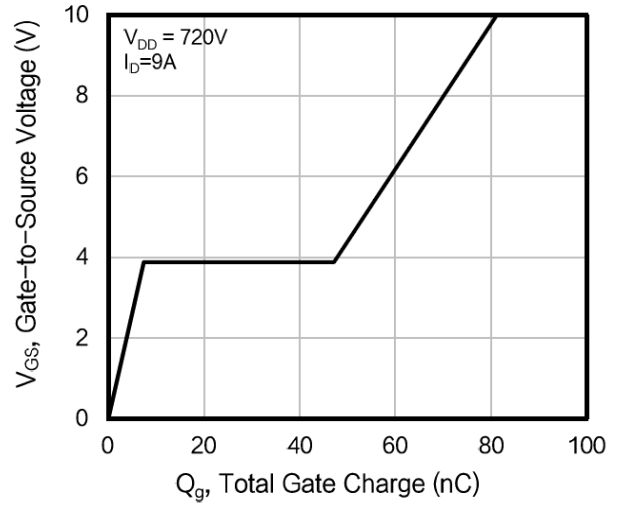
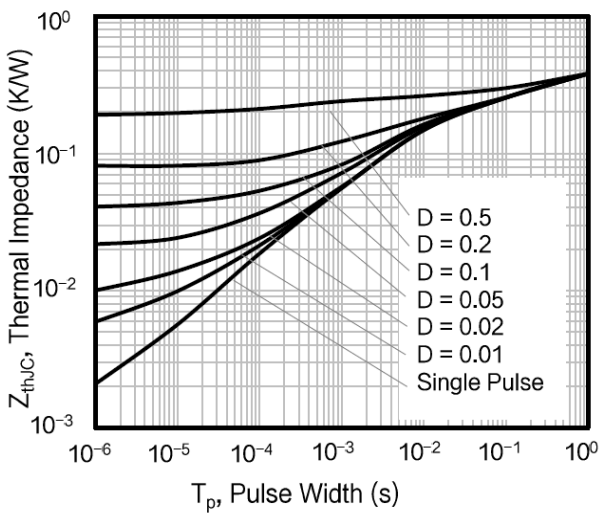
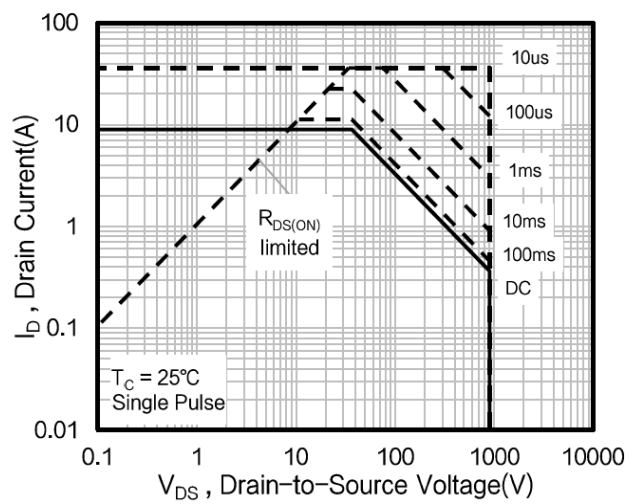
Electrical Characteristics ($T_J=25^{\circ}\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	900	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=720V, V_{GS}=0V$	---	---	1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	---	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=4.5A$	---	0.95	1.25	Ω
Dynamic Characteristics ^⑤						
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ $Freq.=1MHz$	---	2100	---	pF
C_{oss}	Output Capacitance		---	190	---	
C_{rss}	Reverse Transfer Capacitance		---	33	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=450V, V_{GS}=10V,$ $R_G=25\Omega, I_D=9A$	---	51	---	nS
T_r	Turn-on Rise Time		---	43	---	
$T_{d(off)}$	Turn-off Delay Time		---	320	---	
T_f	Turn-off Fall Time		---	75	---	
Q_g	Total Gate Charge	$V_{DD}=720V,$ $V_{GS}=10V, I_D=9A$	---	81	---	nC
Q_{gs}	Gate-Source Charge		---	7.6	---	
Q_{gd}	Gate-Drain Charge		---	38	---	
Source-Drain Characteristics ($T_J=25^{\circ}\text{C}$)						
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=4.5A, T_J=25^{\circ}\text{C}$	---	0.8	1.4	V
t_{rr}	Reverse Recovery Time	$I_S=9A,$ $di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	---	540	---	nS
Q_{rr}	Reverse Recovery Charge		---	8.5	---	nC

Note ④ : Pulse test (pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$).

Note ⑤ : Guaranteed by design, not subject to production testing.

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Typical Characteristics
Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

Figure 2. Body Diode Forward Voltage

Figure 3. Drain Current vs. Temperature

Figure 4. BV_{DSS} Variation vs. Temperature

Figure 5. Transfer Characteristics

Figure 6. On-Resistance vs. Temperature


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Figure 7. Capacitance

Figure 8. Gate Charge

Figure 9. Transient Thermal Impedance

Figure 10. Safe Operating Area


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TO-220 Package Outline Data


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.350	4.650
A1	2.250	2.550
b	0.710	0.910
b1	1.170	1.400
c	0.330	0.650
c1	1.200	1.400
D	9.910	10.250
E	8.9500	9.750
E1	12.650	12.950
e	2.540 TYP.	
e1	4.980	5.180
F	2.650	2.950
H	7.900	8.100
h	0.000	0.300
L	12.700	13.500
L1	2.850	3.250
V	7.500 REF.	
Φ	3.400	3.800